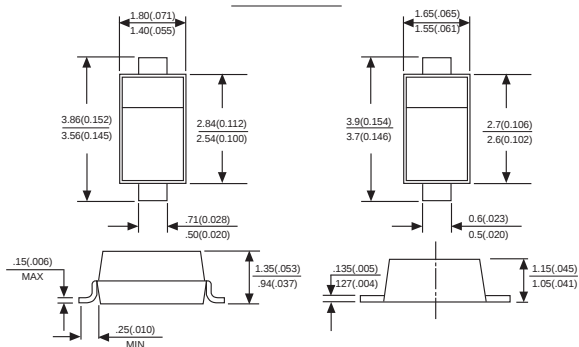


SD103AW-SD103CW

SCHTTKY DIODES

SOD-123



Dimensions in millimeters and (inches)

FEATURES

- ◆ Low forward voltage drop
- ◆ Guard ring construction for transient protection
- ◆ Negligible reverse recovery time
- ◆ low reverse capacitance

MECHANICAL DATA

Case: Molded plastic body

Terminals: Plated leads solderable per MIL-STD-750, Method 2026

Polarity: Polarity symbols marked on case

Mounting Position: Any

Marking: SD103AW:S4, SD103BW:S5, SD103CW:S6

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings and electrical characteristics, Single diode @T_A=25°C

PARAMETER	SYMBOLS	SD103AW	SD103BW	SD103CW	UNITS
Peak repetitive peak reverse voltage	V _{RRM}				
Working peak reverse voltage	V _{RWM}	40	30	20	VOLTS
DC Blocking voltage	V _{DC}				
RMS Reverse voltage	V _{R(RMS)}	28	21	14	V
Forward continuous current	I _{FM}		350		mA
Repetitive peak forward current @t≤1.0s	I _{FRM}		1.5		A
Power dissipation	P _d		400		mW
Thermal resistance junction to ambient	R _{θJA}		300		°C/W
Storage temperature	T _{STG}		-65 to +125		°C

Electrical ratings @T_A=25°C

PARAMETER	SYMBOLS	Min.	Typ.	Max.	Unit	Conditions
Reverse breakdown voltage	SD103AW SD103BW SD103CW V _{(BR)R}	40 30 20			V	IR=100uA IR=100uA IR=100uA
Foward voltage	V _F			0.37 0.60	V	I _F =20mA I _F =200mA
Reverse current	SD103AW SD103BW SD103CW I _{RM}			5.0	uA	V _R =30V V _R =20V V _R =10V
Capacitance between terminals	C _T		50		pF	V _R =0V,f=1.0MHz
Reverse recovery time	t _{rr}		10		ns	I _F =I _R =200mA I _{rr} =0.1X I _R , R _L =100Ω

RATINGS AND CHARACTERISTIC CURVES SD103AW-SD103CW

FIG. 1- TYPICAL FORWARD CHARACTERISTICS

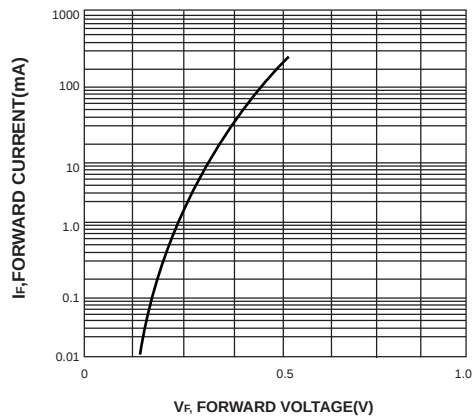


FIG. 2-TYP. JUNCTION CAPACITANCE VS REVERSE VOLTAGE

